

# isc Silicon NPN Power Transistors

## 2SD476N

### DESCRIPTION

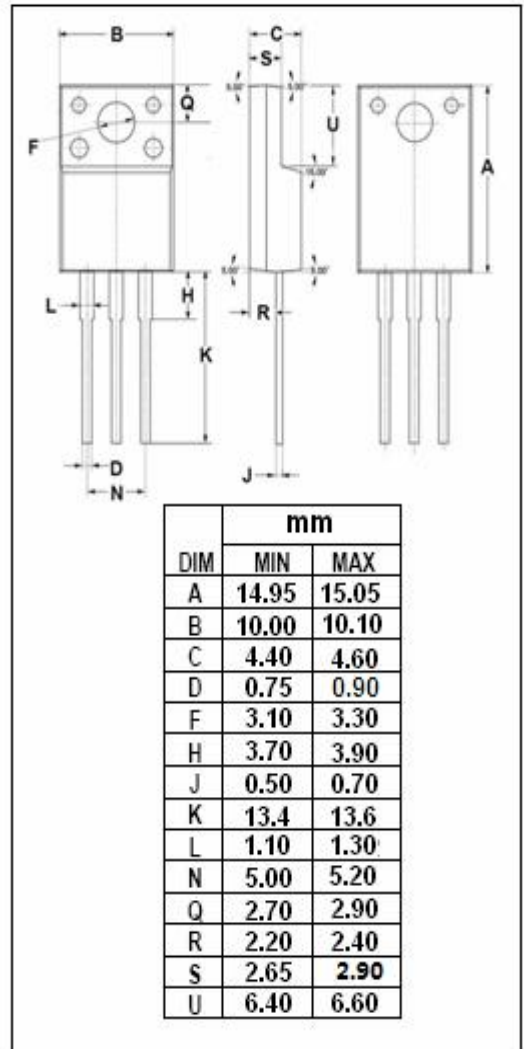
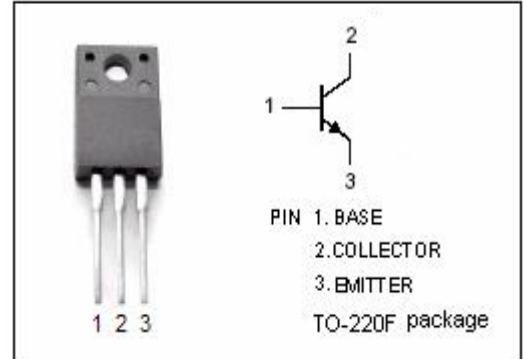
- Low Collector Saturation Voltage  
:  $V_{CE(sat)} = 1.0V(\text{Max}) @ I_C = 2A$
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 50V (\text{Min})$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

- Designed for power switching applications

### ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	70	V
$V_{CEO}$	Collector-Emitter Voltage	50	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	4	A
$I_{CM}$	Collector Current-Peak	8	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	40	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



**isc Silicon NPN Power Transistors****2SD476N****ELECTRICAL CHARACTERISTICS****T<sub>c</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA ; R <sub>BE</sub> = ∞	50			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 10 μA ; I <sub>E</sub> = 0	70			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10 μA ; I <sub>C</sub> = 0	5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A ; I <sub>B</sub> = 0.2A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A ; I <sub>B</sub> = 0.2A			1.2	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 50V ; I <sub>E</sub> = 0			1.0	μA
h <sub>FE -1</sub>	DC current gain	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 4V	200		300	
h <sub>FE -2</sub>	DC current gain	I <sub>C</sub> =0.1A ; V <sub>CE</sub> = 4V	35			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A ; V <sub>CE</sub> = 4V		7		MHz

**Switching times**

t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = 0.5A ; I <sub>B1</sub> = I <sub>B2</sub> = 50mA ; V <sub>CC</sub> = 10.5V		0.3		μs
t <sub>off</sub>	Turn-off Time			3.0		μs
t <sub>stg</sub>	Fall Time			2.5		μs

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